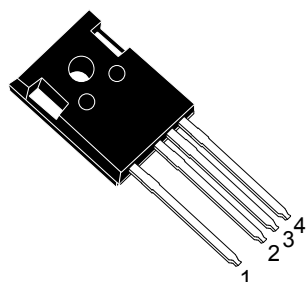
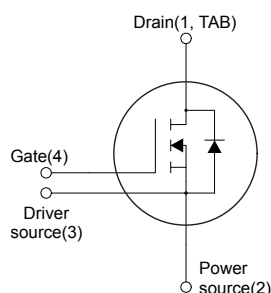


Automotive-grade silicon carbide Power MOSFET 900 V, 12 mΩ typ., 110 A in an HiP247-4 package



HiP247-4



ND1TPS2DS3G4



Features

Order code	V_{DS}	$R_{DS(on)}$ typ.	I_D
SCT012W90G3-4AG	900 V	12 mΩ	110 A

- AEC-Q101 qualified 
- Very low $R_{DS(on)}$ over the entire temperature range
- High speed switching performances
- Very fast and robust intrinsic body diode
- Very high operating junction temperature capability ($T_J = 200\text{ °C}$)
- Source sensing pin for increased efficiency

Applications

- DC/DC converter for EV/HEV
- Main inverter (electric traction)
- On board charger (OBC)

Description

This silicon carbide Power MOSFET device has been developed using ST's advanced and innovative 3rd generation SiC MOSFET technology. The device features a very low $R_{DS(on)}$ over the entire temperature range combined with low capacitances and very high switching operations, which improve application performance in frequency, energy efficiency, system size and weight reduction.

Product status link

[SCT012W90G3-4AG](#)

Product summary

Order code	SCT012W90G3-4AG
Marking	SCT012W90G34AG
Package	HiP247-4
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	900	V
V_{GS}	Gate-source voltage	-10 to 22	V
	Gate-source voltage (recommended operating values)	-5 to 18	
	Gate-source transient voltage, $t_p < 1 \mu s$, $t \leq 10$ hours over lifetime	-11 to 25	
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ C$	110	A
	Drain current (continuous) at $T_C = 100^\circ C$	110	
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
P_{TOT}	Total power dissipation at $T_C = 25^\circ C$	625	W
T_{stg}	Storage temperature range	-55 to 200	$^\circ C$
T_J	Operating junction temperature range		$^\circ C$

1. Limited by bonding wires.

2. Pulse width is limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.28	$^\circ C/W$
R_{thJA}	Thermal resistance, junction-to-ambient	40	$^\circ C/W$

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified.

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	900			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 900\text{ V}$			10	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = -10\text{ to }22\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 10\text{ mA}$	1.8	3.1	4.2	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 15\text{ V}$, $I_D = 60\text{ A}$		13.4		m Ω
		$V_{GS} = 18\text{ V}$, $I_D = 60\text{ A}$		12	15.8	
		$V_{GS} = 18\text{ V}$, $I_D = 60\text{ A}$, $T_J = 200\text{ °C}$		20.3		

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 600\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	3880	-	pF
C_{oss}	Output capacitance		-	244	-	pF
C_{rss}	Reverse transfer capacitance		-	20	-	pF
Q_g	Total gate charge	$V_{DD} = 600\text{ V}$, $V_{GS} = -5\text{ to }18\text{ V}$, $I_D = 60\text{ A}$	-	138	-	nC
Q_{gs}	Gate-source charge		-	43	-	nC
Q_{gd}	Gate-drain charge		-	44	-	nC
R_g	Gate input resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	1.8	-	Ω

Table 5. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	$V_{DD} = 600\text{ V}$, $I_D = 60\text{ A}$,	-	446	-	μJ
E_{off}	Turn-off switching energy	$R_G = 5.6\text{ }\Omega$, $V_{GS} = -5\text{ V to }18\text{ V}$	-	341	-	μJ

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 600\text{ V}$, $I_D = 60\text{ A}$, $R_G = 5.6\text{ }\Omega$, $V_{GS} = -5\text{ to }18\text{ V}$	-	27.4	-	ns
t_r	Rise time		-	13.2	-	ns
$t_{d(off)}$	Turn-off delay time		-	60.7	-	ns
t_f	Fall time		-	29	-	ns

Table 7. Reverse SiC diode characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Continuous diode forward current	$T_C = 25\text{ }^{\circ}\text{C}$	-		110	A
		$T_C = 100\text{ }^{\circ}\text{C}$	-		110	
V_{SD}	Diode forward voltage	$I_{SD} = 60\text{ A}$, $V_{GS} = 0\text{ V}$	-	2.8		V
t_{rr}	Reverse recovery time	$I_{SD} = 60\text{ A}$, $di/dt = 1000\text{ A}/\mu\text{s}$, $V_{DD} = 600\text{ V}$	-	26		ns
Q_{rr}	Reverse recovery charge		-	257		nC
I_{RRM}	Reverse recovery current		-	18.3		A

1. Limited by bonding wires.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

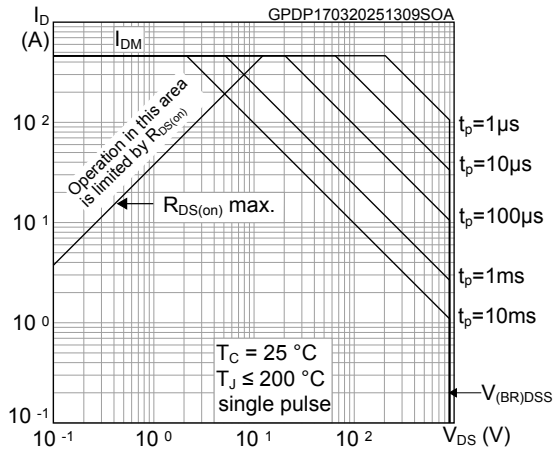


Figure 2. Maximum transient thermal impedance

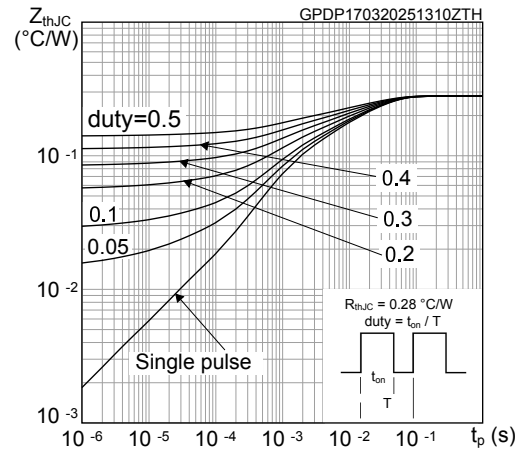


Figure 3. Typical output characteristics ($T_J = 25\text{ °C}$)

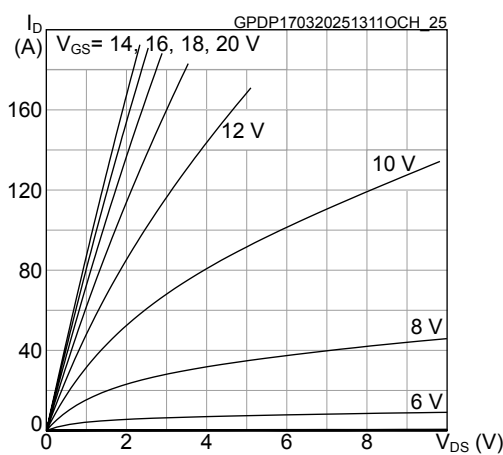


Figure 4. Typical output characteristics ($T_J = 200\text{ °C}$)

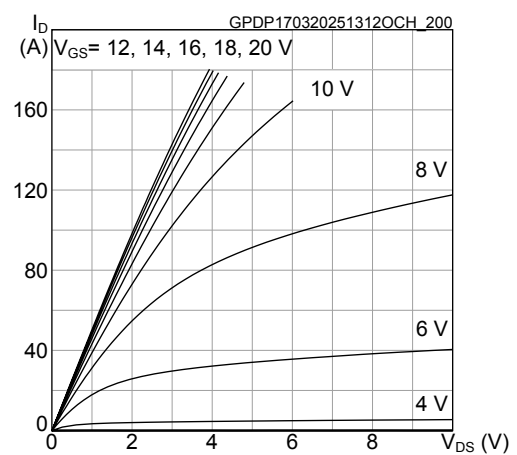


Figure 5. Typical transfer characteristics

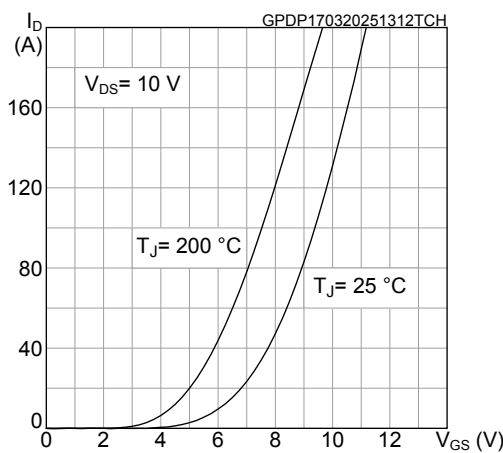


Figure 6. Total power dissipation

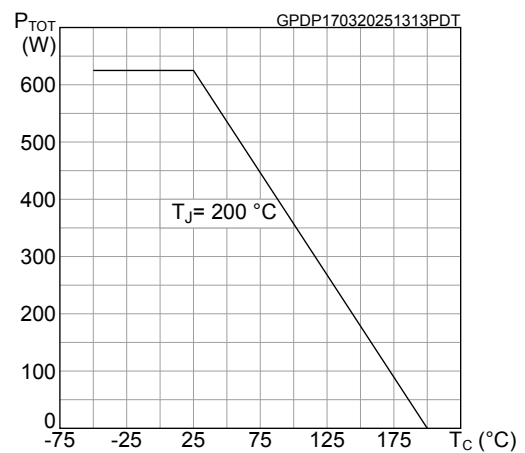


Figure 7. Maximum continuous drain current vs case temperature

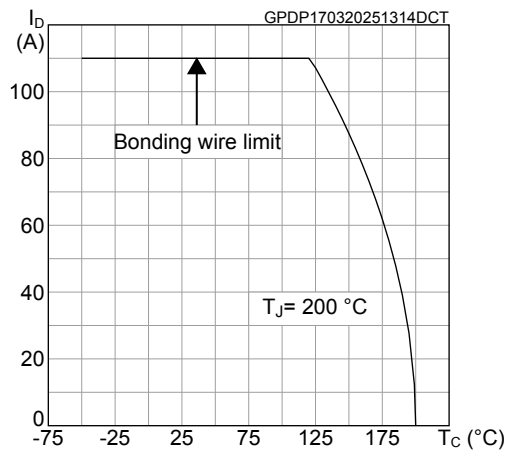


Figure 8. Typical gate charge characteristics

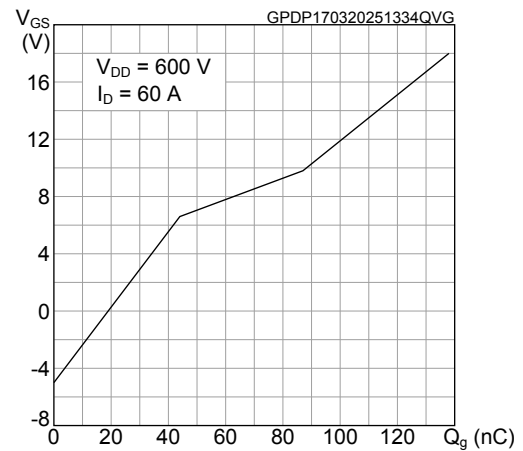


Figure 9. Typical capacitance characteristics

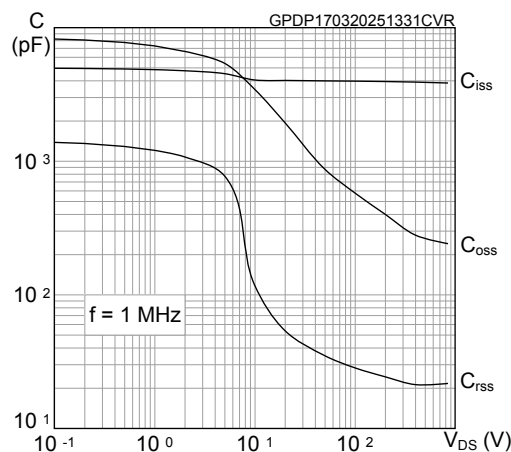


Figure 10. Typical switching energy vs drain current

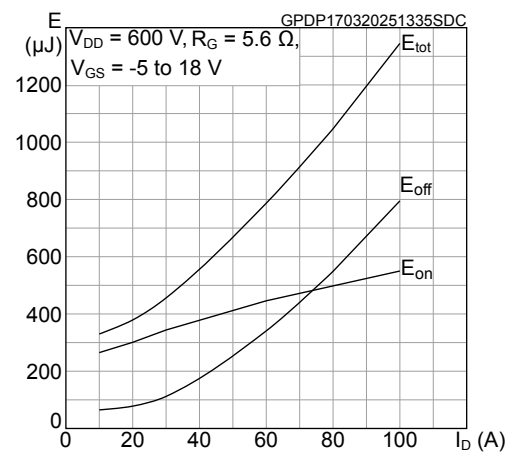


Figure 11. Typical switching energy vs gate resistance

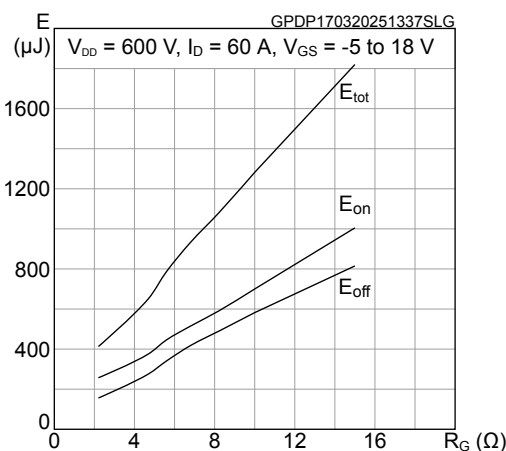


Figure 12. Typical switching energy vs temperature

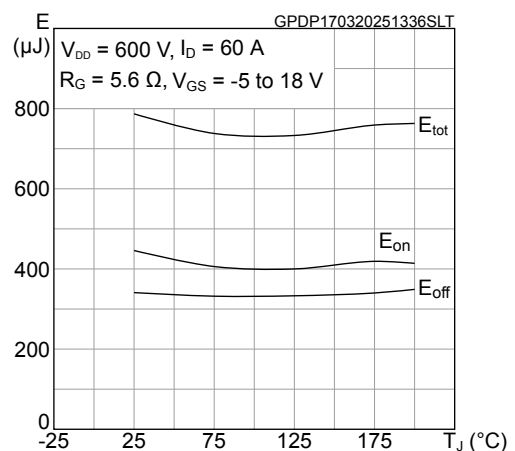
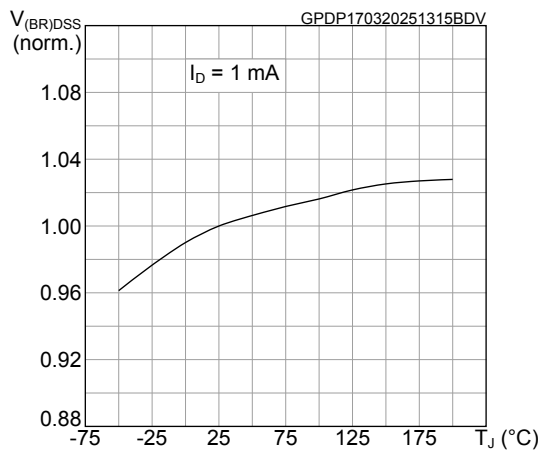
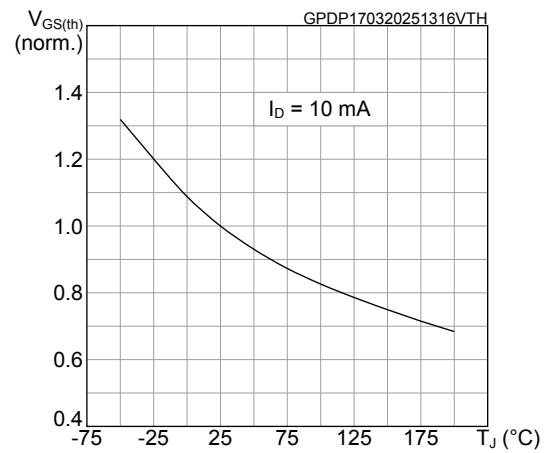
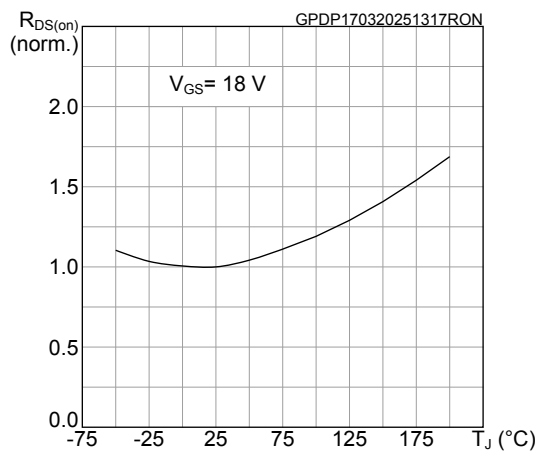
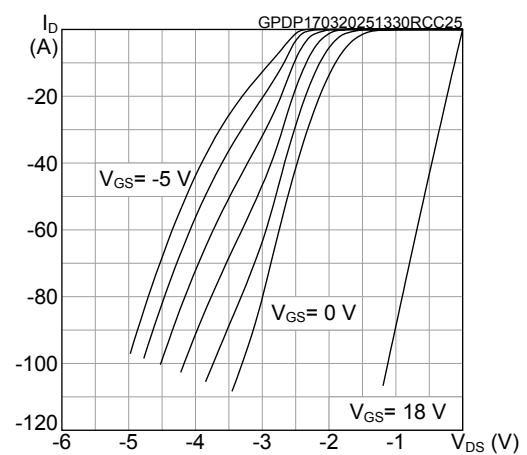
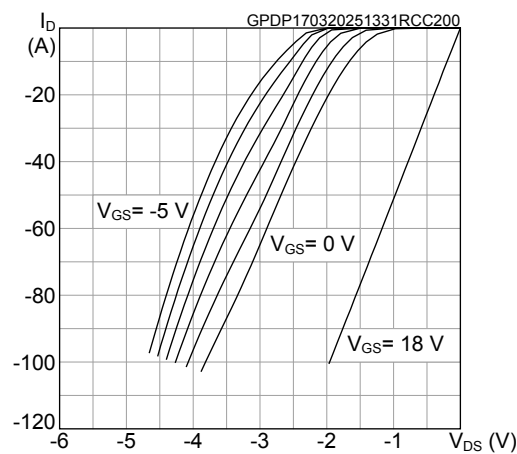


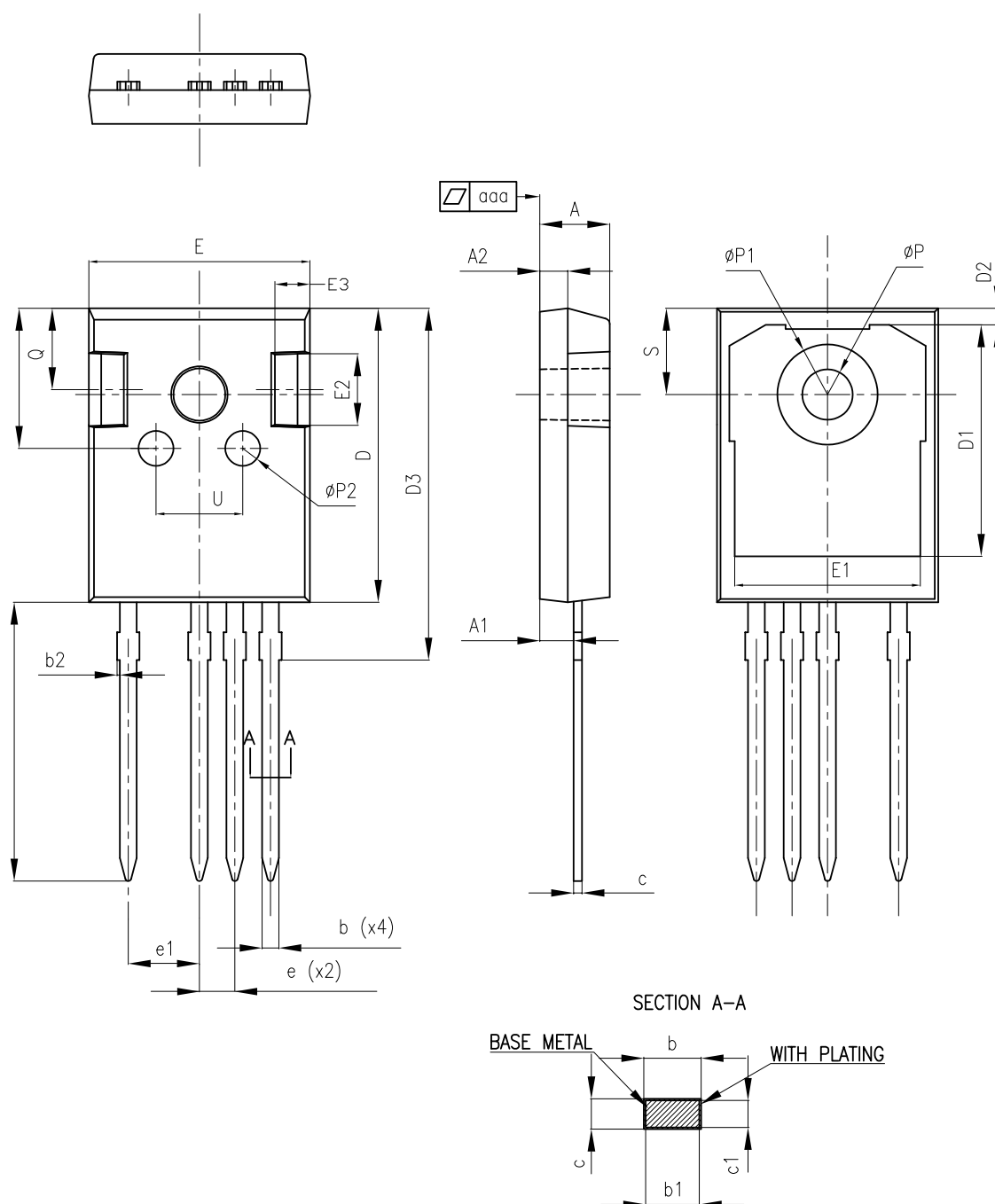
Figure 13. Normalized breakdown voltage vs temperature

Figure 14. Normalized gate threshold vs temperature

Figure 15. Normalized on-resistance vs temperature

Figure 16. Typical reverse conduction characteristics (T_J = 25 °C)

Figure 17. Typical reverse conduction characteristics (T_J = 200 °C)


3 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

3.1 HiP247-4 package information

Figure 18. HiP247-4 package outline



8405626_Rev_6

Table 8. HiP247-4 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.29
b1	1.15	1.20	1.25
b2	0		0.20
c	0.59		0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
D3	24.97	25.12	25.27
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	2.44	2.54	2.64
e1	4.98	5.08	5.18
L	19.80	19.92	20.10
P	3.50	3.60	3.70
P1			7.40
P2	2.40	2.50	2.60
Q	5.60		6.00
S		6.15	
T	9.80		10.20
U	6.00		6.40
aaa		0.04	0.10

Revision history

Table 9. Document revision history

Date	Revision	Changes
18-Mar-2025	1	First release.

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